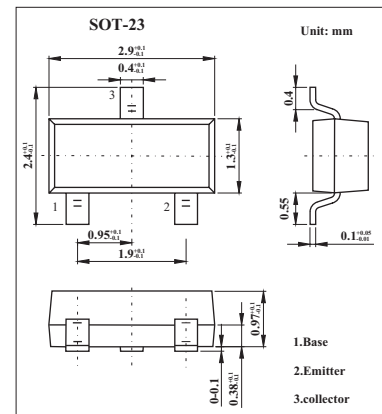


Silicon NPN Epitaxial

2SD1101

■ Features

- Low Frequency amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	25	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	0.7	A
Collector peak current	i _{c(peak)}	1	A
Collector dissipation	P _c	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c = 10μA , I _E = 0	25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c = 1mA , R _{BE} = ∞	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA , I _c = 0	5			V
Collector cutoff current	I _{cBO}	V _{CB} = 20V , I _E = 0			1.0	μA
DC current gain	h _{FE}	V _{CE} = 1V , I _c = 0.15A	85		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = 0.5A , I _B = 0.05A			0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 1V , I _c = 0.15A			1.0	V

■ hFE Classification

Marking	AB	AC
hFE	85~170	120~240